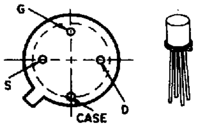
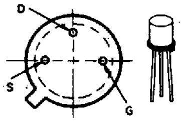
Field Effect Transistors (cont'd) (Observe MOS Handling) ▲

ECG Type	Description and Application	Transcon-ductance gfs µmhos	Gate to Source Cutoff Voltage V_{GS} (off) Max V	Zero-Gate Drain Current I_{DSS}	Drain Current I_D	Input Cap C_{iss} Max pf	Gate to Source Breakdown Voltage BV_{GSS} Min V	Drain to Source Resistance r_{DS} (on) Max ohms	Device Diss. P_D Max mW	Package Case/Fig./Basing
ECG464 ▲ DISCONTINUED	MOSFET, P-Ch, Enhancement, Sw, (Compl to ECG465)	1,000 Min	5	10 nA Max	3 mA Min (on)	5	25	600	300	**TO-72** Fig. T4 
						td 60 ns; tr 65 ns; t(off) 60 ns				
ECG465 ▲	MOSFET, N-Ch, Enhancement, Sw (Compl to ECG464)	1,000 Min	5	10 nA Max	3 mA Min (on)	5	25	300	300	
						td 60 ns; tr 65 ns; t(off) 60 ns				
ECG466	JFET, N-Ch, Chopper/Sw	---	10	50 mA Min	250 pA Max (off)	18	40	25	360	**TO-18** Fig. T2 
						td 6 ns; tr 3 ns; t(off) 25 ns				
ECG467	JFET, N-Ch, Chopper/ Fast Sw	---	---	50 mA Min	1.0 nA Max (off)	10	30	30	310	**TO-92** Fig. T16 
						td 4 ns; tr 5 ns; t(off) 5 ns				
ECG468	JFET, N-Ch, Chopper/Sw	8,000	10	20 mA Min	1.0 nA Max (off)	16	35	30	360	
						td 7 ns; tr 6 ns; t(off) 20 ns				
ECG469	JFET, N-Ch, Chopper/Sw	7,500	3	2 mA Min	1.0 nA Max (off)	16	35	100	360	
						td 7 ns; tr 6 ns; t(off) 20 ns				

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MOSFETS

ECG Type	Description and Application	Transcon-ductance gfs µmhos	Drain to Source Breakdown Voltage BV_{DSS}	Gate to Source Breakdown Voltage BV_{GS}	Continuous Drain Current I_D Amps	Gate to Source Threshold Voltage V_{GS} (th)	Drain to Source Resistance r_{DS} (on) Ohms	Input Cap C_{iss} pf	Device Dissipation @T_C=25° C P_D mW	Package Case/Fig./ Basing
ECG490 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	200,000	60	± 15	.5	3	5	40	830	**TO-92** Fig. T16  Note: ECG491 Basing is S,G,D
						td(off) = 10 ns, td(on) =10 ns				
ECG491 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	100,000	60	± 40	.28	3	5	40	830	
						td(off) = 10 ns, td(on) = 10 ns				
ECG492 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	200,000	200	± 20	.25	3	6.5	45	600	
						td(off) = 10 ns, td(on) = 10 ns				

▲ Refer to MOSFET Handling Precautions - Page 1 - 34

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